Silicon PNP Epitaxial

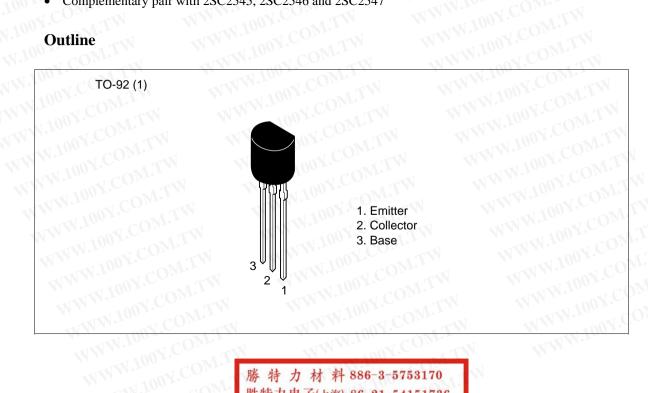
# HITAC

## **Application**

Y.COM

- Low frequency low noise amplifier
- Complementary pair with 2SC2545, 2SC2546 and 2SC2547

#### N.100Y **Outline**



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# **Absolute Maximum Ratings** (Ta = 25°C)

Item	Symbol	2SA1083	2SA1084	2SA1085	Uni
Collector to base voltage	$V_{\text{CBO}}$	-60	<b>-90</b>	-120	V
Collector to emitter voltage	V <sub>CEO</sub>	-60	-90	-120	V
Emitter to base voltage	$V_{EBO}$	<b>-</b> 5	-5	<b>-</b> 5	V
Collector current	I <sub>c</sub>	-100	-100	-100	mΑ
Emitter current	OX. PE	100	100	100	mA
Collector power dissipation	P <sub>c</sub>	400	400	400	mW
Junction temperature	Tj.CON	150	150	150	°C
Storage temperature	Tstg	-55 to +150	-55 to +150	-55 to +150	°C

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#### **Electrical Characteristics** ( $Ta = 25^{\circ}C$ )

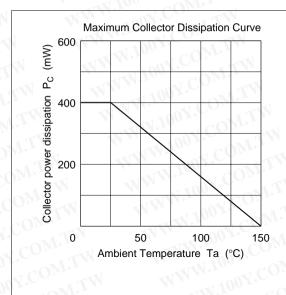
		2SA1083		2SA1084		2SA1	2SA1085					
Item	Symbol	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	V <sub>(BR)CBO</sub>	-60	OM.	L <del>A</del> N	-90	-11		-120	Z.C	OM	V	$I_{\rm C} = -10 \; \mu \text{A}, \; I_{\rm E} = 0$
Collector to emitter breakdown voltage	V <sub>(BR)CEO</sub>	-60		1.T\	-90	_	WW	-120	001	.eoī	V	$I_C = -1 \text{ mA},$ $R_{BE} = \infty$
Emitter to base breakdown voltage	V <sub>(BR)EBO</sub>	-5	Co.	$\overline{\Lambda}$ . $\overline{\Lambda}$	-5	_	-VI	-5	100	7.0°	V.	$I_E = -10 \mu A, I_C = 0$
Collector cutoff current	I <sub>CBO</sub>	700	<u>*</u> C	-0.1	T XX	_	-0.1		$TI_{B}$	-0.1	μА	$V_{CB} = -50 \text{ V}, I_{E} = 0$
Emitter cutoff current	I <sub>EBO</sub>	440	0 7.	-0.1	(7,	<u>√</u>	-0.1	47 -41 VN	41.1	-0.1	μΑ	$V_{EB} = -2 \text{ V}, I_{C} = 0$
DC current transfer ratio	h <sub>FE</sub> *1	250	1002 0 <u>0</u> 2	800	250	TW.	800	250	NN	800	Y.CC	$V_{CE} = -12 \text{ V},$ $I_{C} = -2 \text{ mA}$
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	NIN	V.100	-0.2	OM DE	IN	<b>-0.2</b>	-4		-0.2	V.C	$I_C = -10 \text{ mA},$ $I_B = -1 \text{ mA}$
Base to emitter voltage	$V_{BE}$	NW	-0.6	00 A	$CO_J$	-0.6	N	_	-0.6	V <del>V</del> V.)	100	$V_{CE} = -12 \text{ V},$ $I_{C} = -2 \text{ mA}$
Gain bandwidth product	f <sub>T</sub>	W	90	100	1.C0	90	14/	_	90		MHz	$V_{CE} = -12 \text{ V},$ $I_{C} = -2 \text{ mA}$
Collector output capacitance	Cob		3.5	N-101	10 X .	3.5	17	N	3.5	WW	pF	$V_{CB} = -10 \text{ V}, I_{E} = 0,$ f = 1 MHz
Noise voltage reffered to input	e <sub>n</sub>	_	0.5	MM:	.100. Tanj	0.5	M.T.M.O.M.O.M.O.M.O.M.O.M.O.M.O.M.O.M.O.	TW	0.5	-V	nV/ √Hz	$V_{CE} = -6V,$ $I_{C} = -10 \text{ mA},$ $f = 1 \text{ kHz},$ $R_{g} = 0, \Delta f = 1 \text{Hz}$

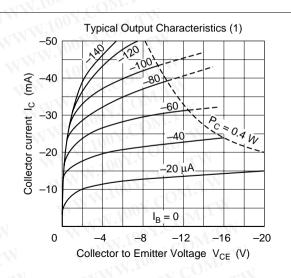
Note: 1. The 2SA1083, 2SA1084 and 2SA1085 are grouped by h<sub>FE</sub> as follows.

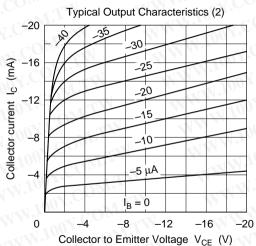
D E 250 to 500 400 to 800

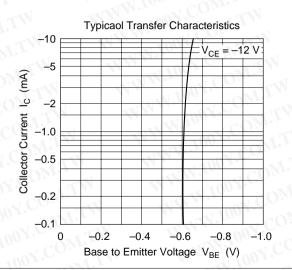
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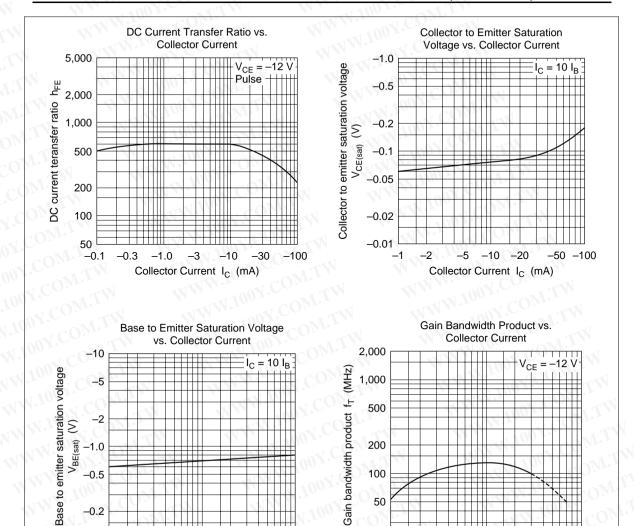








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20

-2

-5

-10 -20

Collector Current I<sub>C</sub> (mA)

-50

-0.2-0.1

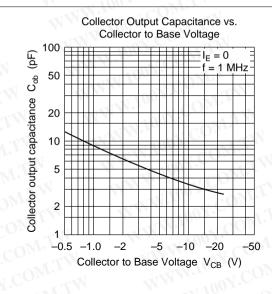
-5

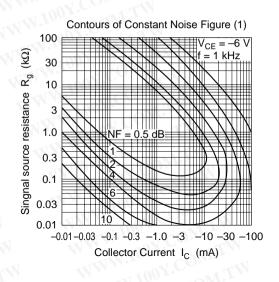
-10

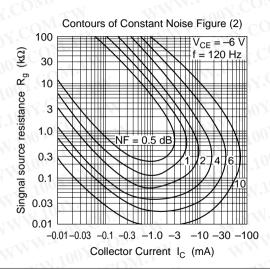
Collector Current I<sub>C</sub> (mA)

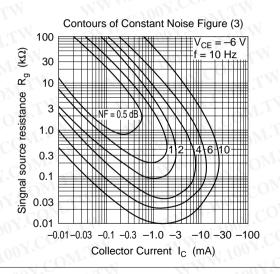
-20

-50 -100



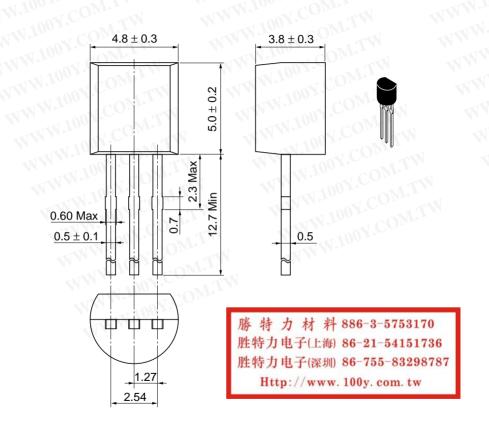






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Unit: mm



Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.25 g

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